Docket No.: 055071-0329

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277

Doug van den BROEKE, et al. : Confirmation Number: 3769

Application No.: 10/756,830 : Group Art Unit: 2891

Filed: January 14, 2004 : Examiner: EVERHART, CARIDAD

For: METHOD AND APPARATUS FOR PROVIDING OPTICAL PROXIMITY FEATURES TO A RETICLE PATTERN FOR DEEP SUB-WAVELENGTH OPTICAL LITHOGRAPHY

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed more than three months after the U.S. filing date AND after the mailing date of the first Office Action on the merits, but before the mailing date of a Final Rejection or Notice of Allowance.

03/03/2006 HALI11 00000103 500417 10756830 01 FC:1806 180.00 DA

10/756,830

In accordance with 37 CFR 1.17(p), please charge the fee of \$180.00 to Deposit Account No. 500417.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Facsimile: 202.756.8087 **Date: March 2, 2006**

Please recognize our Customer No. 20277 as our correspondence address.

SHEET 1 OF 1

INFORMATION DISCLO CITATION IN AN APPLICATION

ATTY. DOCKET NO. **055071-0329**

SERIAL NO. **10/756,830**

APPLICANT

Doug van den BROEKE, et al.

(PTO-1449)

FILING DATE

GROUP

January 14, 2004

2891

U.S. PATENT DOCUMENTS

	NO.	Document Number Number-Kind Code2 (# known) US 5,895,741		Publication Date MM-DD-YYYY	Name of Patentee or Applic Document		Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
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		-	OTHER A	RT (Including Autho	r, Title, Date, Pertinent Pages, Et	c.)		
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.						9,
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¹ Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.